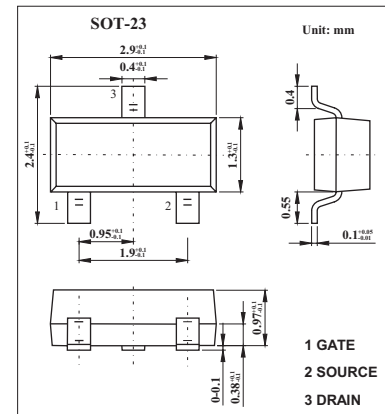


N-Channel Enhanceent Mode Field Effect Transistor 2N7002K

■ Features

- Low On-Resistance: $R_{DS(ON)}$
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage



■ Absolute Maximum Ratings $T_a=25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	60	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current -Continuous	I_D	300	mA
Drain Current -Pulsed		800	mA
Power Dissipation	P_D	350	mW
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	357	$^\circ\text{C/W}$
Operating and Storage Temperature Range	T_j, T_{STG}	-65 to +150	$^\circ\text{C}$

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0V, I_D = 10 \mu A$	60			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 60V, V_{GS} = 0V$			1.0	μA
Gate-Body Leakage	I_{GSS}	$V_{GS} = \pm 20V, V_{DS} = 0V$			± 10	μA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = 10V, I_D = 1mA$	1.0	1.6	2.5	V
Static Drain-Source On-Resistance	$R_{DS(ON)}$	$V_{GS} = 10V, I_D = 0.5A$			2.0	Ω
		$V_{GS} = 5V, I_D = 0.05A$			3.0	
Forward Transfer Admittance	$ Y_{fs} $	$V_{GS} = 10V, V_{DS} = 0.2V$	80			ms
Input Capacitance	C_{iss}	$V_{DS} = 25V, V_{GS} = 0V, f = 1.0MHz$			50	pF
Output Capacitance	C_{oss}				25	pF
Reverse Transfer Capacitance	C_{rss}				5.0	pF

■ Marking

Marking	K7K
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